

## Silicon Diffused Power Transistor

BU2525DW

## GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor with integrated damper diode in a plastic envelope intended for use in horizontal deflection circuits of large screen colour television receivers up to 32 kHz.

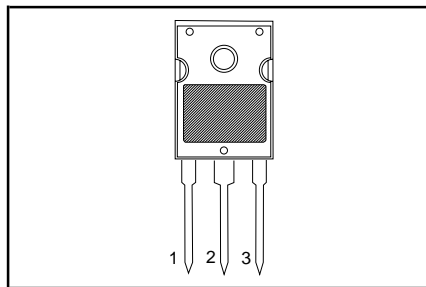
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0$	-	1500	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	800	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	30	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	125	W
$V_{CESat}$	Collector-emitter saturation voltage	$I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	-	5.0	V
$I_{Csat}$	Collector saturation current		8	-	A
$t_s$	Storage time	$I_{Csat} = 8.0\text{ A}; I_{B(end)} = 1.1\text{ A}$	3.0	4.0	$\mu\text{s}$

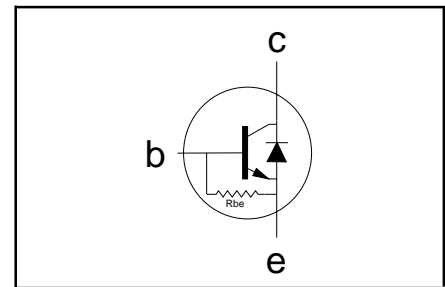
## PINNING - SOT429

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	800	V
$I_C$	Collector current (DC)		-	12	A
$I_{CM}$	Collector current peak value		-	30	A
$I_B$	Base current (DC)		-	8	A
$I_{BM}$	Base current peak value		-	12	A
$-I_{B(AV)}$	Reverse base current	average over any 20 ms period	-	200	mA
$-I_{BM}$	Reverse base current peak value <sup>1</sup>		-	9	A
$P_{tot}$	Total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C}$	-	125	W
$T_{stg}$	Storage temperature		-65	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Junction to mounting base	-	-	1.0	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	45	-	K/W

<sup>1</sup> Turn-off current.

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**STATIC CHARACTERISTICS**

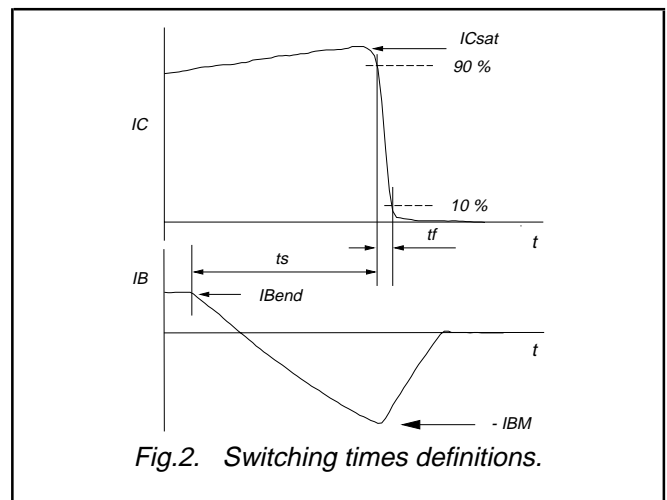
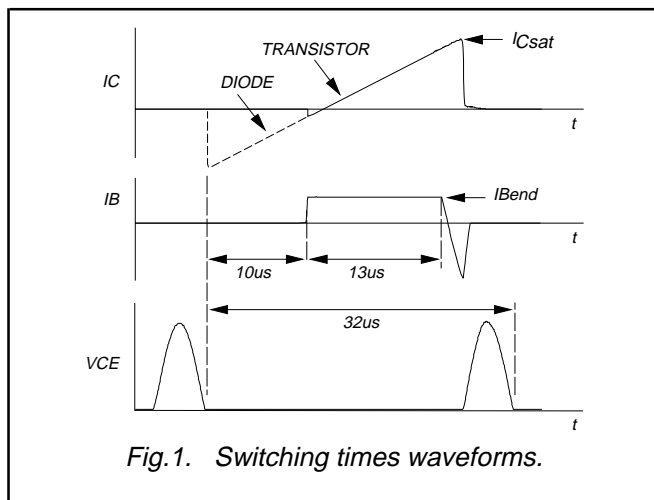
$T_{mb} = 25\text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	Collector cut-off current <sup>2</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	1.0	mA
$I_{CES}$		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^\circ\text{C}$	-	-	2.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 6.0\text{ V}; I_C = 0\text{ A}$	72	110	218	mA
$R_{EB}$	Base-emitter resistance	$V_{EB} = 6.0\text{ V}$	-	55	-	$\Omega$
$BV_{EBO}$	Emitter-base breakdown voltage	$I_B = 600\text{ mA}$	7.5	13.5	-	V
$V_{CEOsust}$	Collector emitter-sustaining voltage	$I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$	800	-	-	V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	-	-	5.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = 8.0\text{ A}; I_B = 1.6\text{ A}$	-	-	1.1	V
$h_{FE}$	DC current gain	$I_C = 1\text{ A}; V_{CE} = 5\text{ V}$	-	11	-	
$h_{FE}$		$I_C = 8\text{ A}; V_{CE} = 5\text{ V}$	5	7	9.5	
$V_F$	Diode forward voltage	$I_F = 8\text{ A}$	-	1.6	2.0	V

**DYNAMIC CHARACTERISTICS**

$T_{mb} = 25\text{ }^\circ\text{C}$  unless otherwise specified

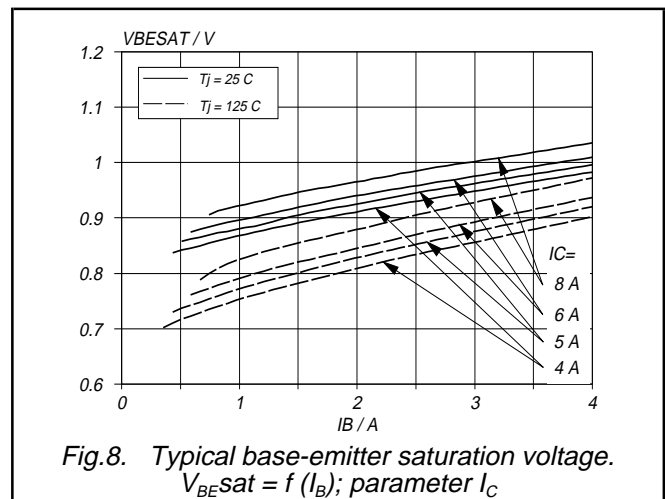
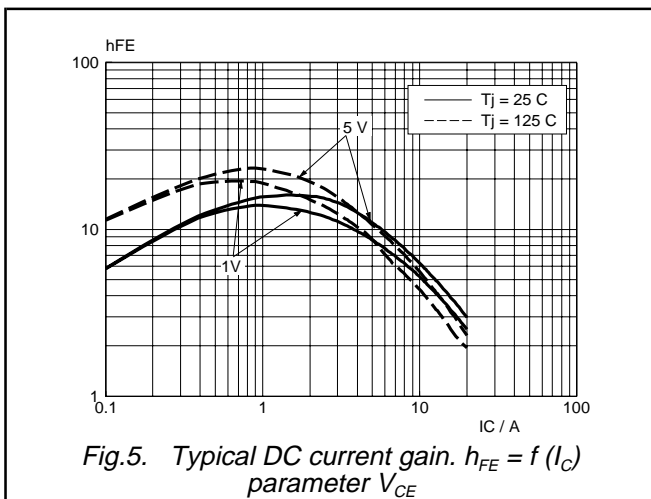
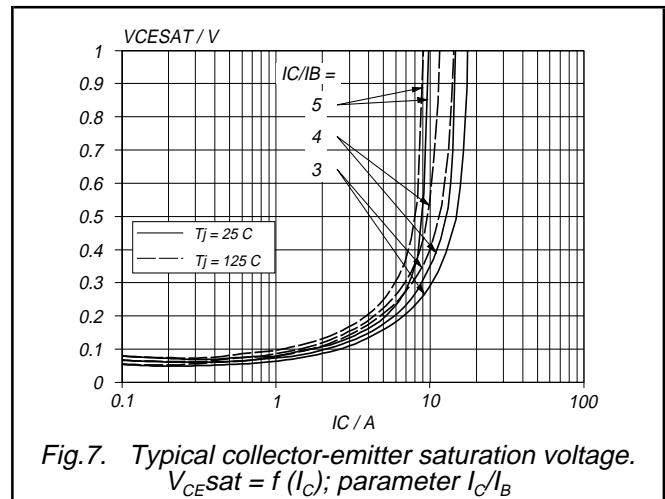
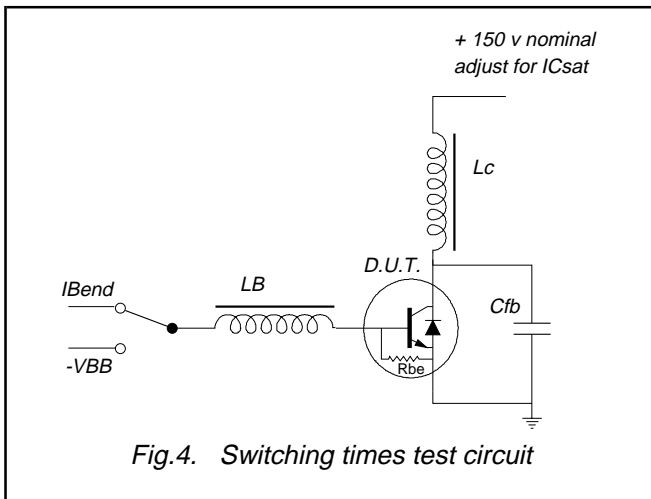
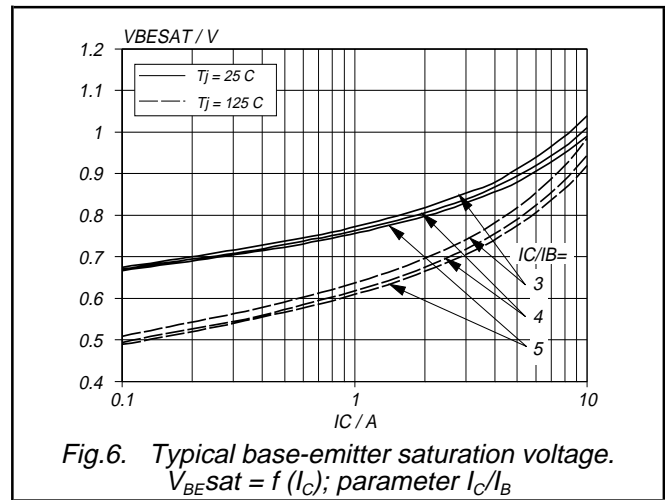
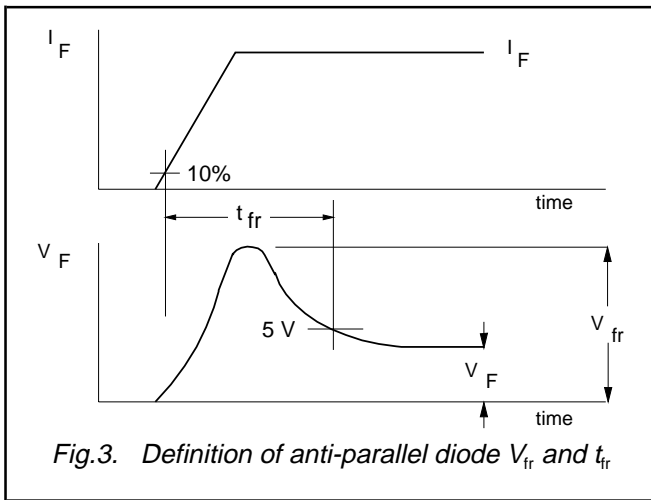
SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$C_c$	Collector capacitance	$I_E = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	145	-	pF
$t_s$	Turn-off storage time	$I_{Csat} = 8.0\text{ A}; L_C = 260\text{ }\mu\text{H}; C_{fb} = 13\text{ nF};$ $I_{B(end)} = 1.1\text{ A}; L_B = 2.5\text{ }\mu\text{H}; -V_{BB} = 4\text{ V};$ $(-di_B/dt = 1.6\text{ A}/\mu\text{s})$	3.0	4.0	$\mu\text{s}$
$t_f$	Turn-off fall time		0.2	0.35	$\mu\text{s}$
$V_{fr}$	Anti-parallel diode forward recovery voltage	$I_F = 8\text{ A}; di_F/dt = 50\text{ A}/\mu\text{s}$	16		V
$t_{fr}$	Anti-parallel diode forward recovery time	$V_F = 5\text{ V}$	410		ns



<sup>2</sup> Measured with half sine-wave voltage (curve tracer).

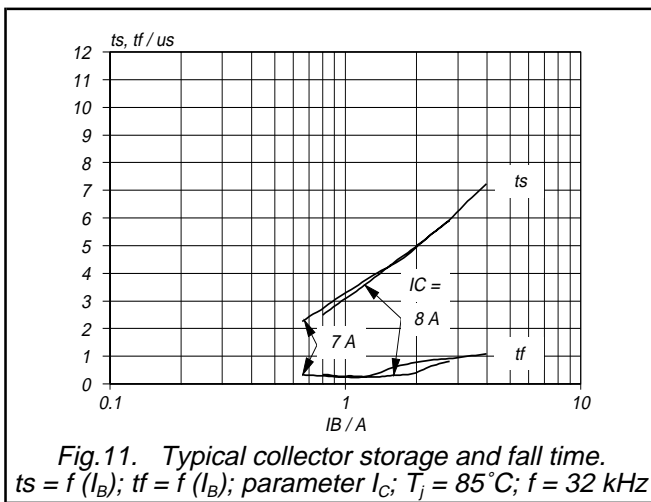
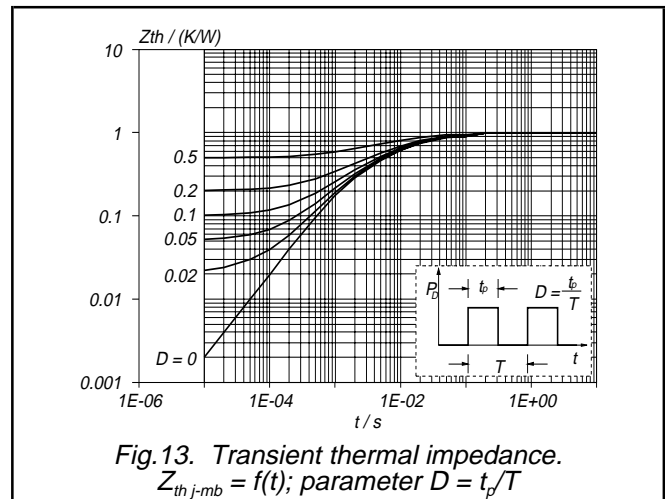
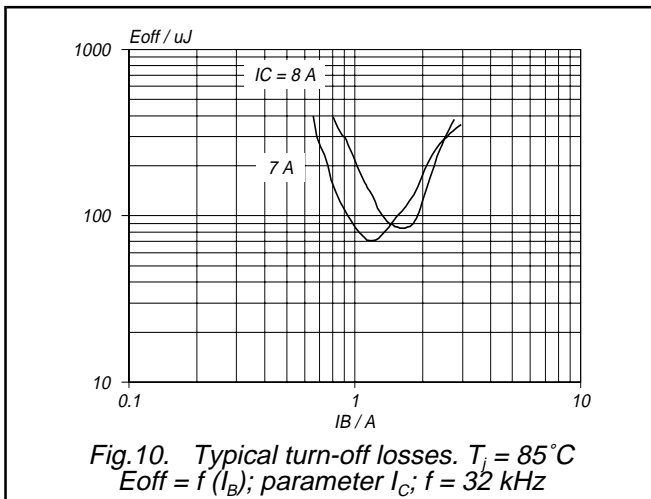
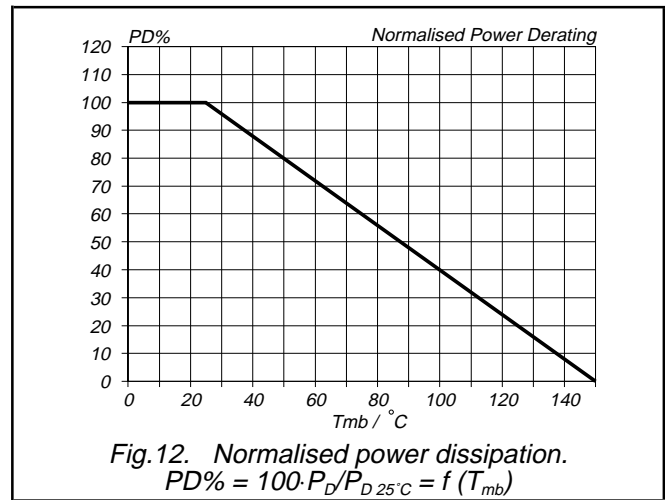
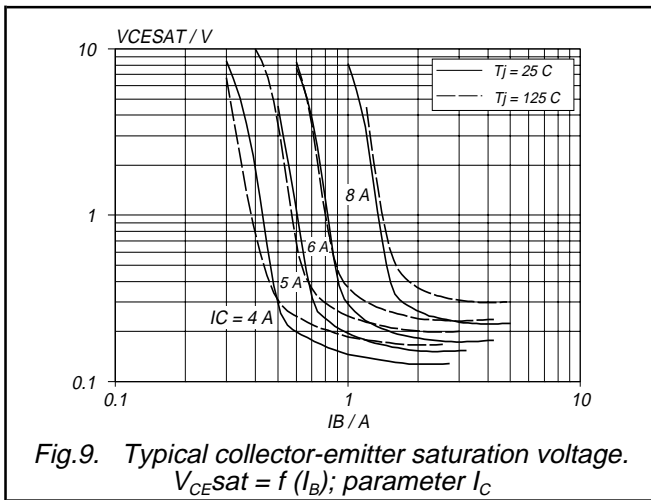
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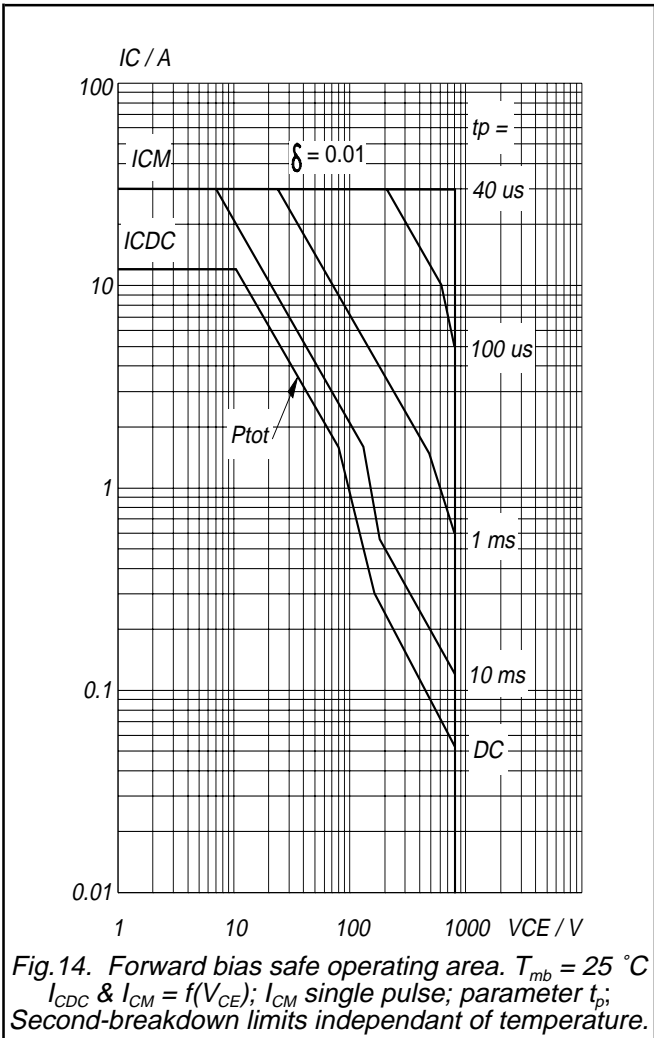
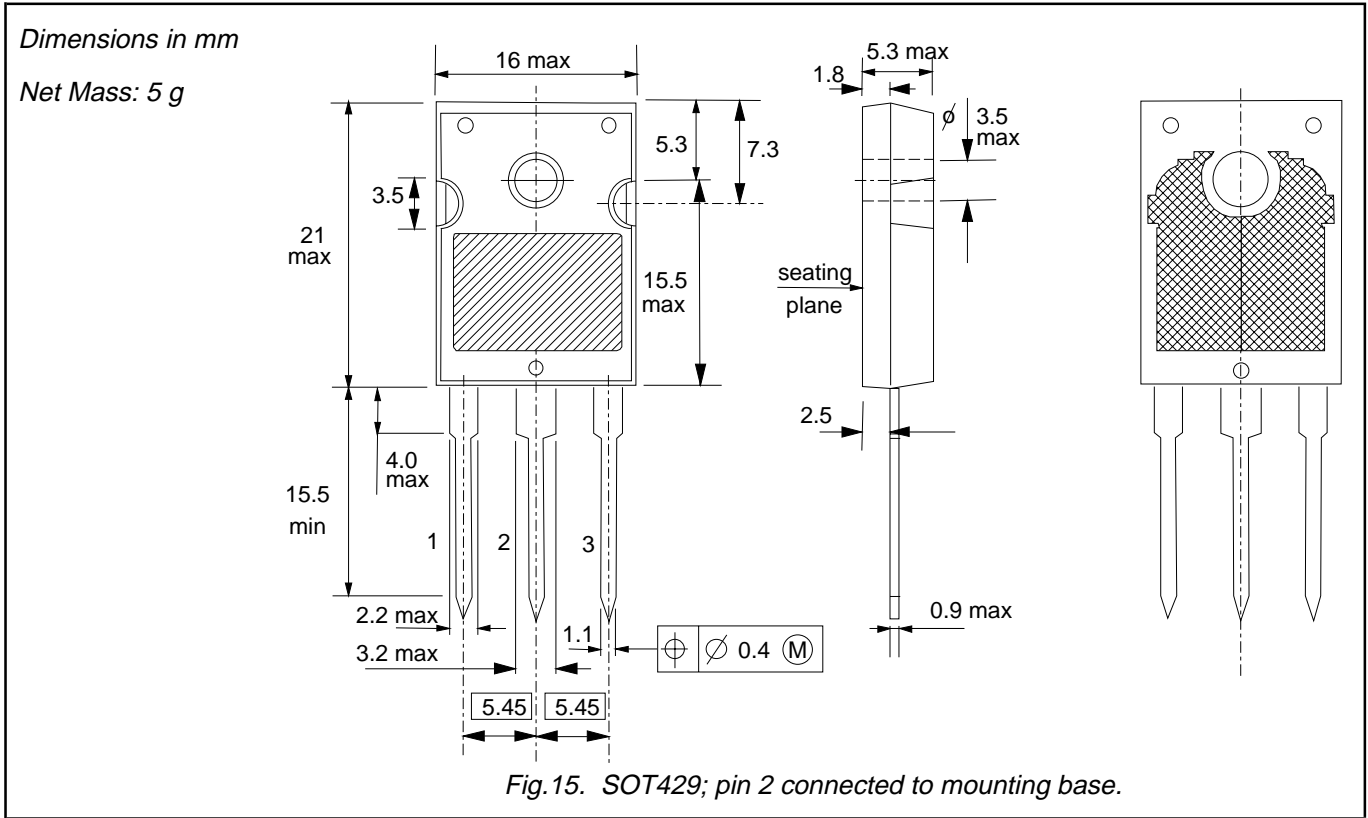


Fig.14. Forward bias safe operating area.  $T_{mb} = 25^\circ C$   
 $I_{CDC}$  &  $I_{CM} = f(V_{CE})$ ;  $I_{CM}$  single pulse; parameter  $t_p$ ;  
Second-breakdown limits independant of temperature.

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MECHANICAL DATA



Notes

- 1. Refer to mounting instructions for SOT429 envelope.
- 2. Epoxy meets UL94 V0 at 1/8".

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**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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